

ORDERING INFORMATION

Device	Temperature Range	Package
MC1550F	-55°C to +125°C	Ceramic Flat
MC1550G	-55°C to +125°C	Metal Can

MC1550G

RF - IF AMPLIFIER

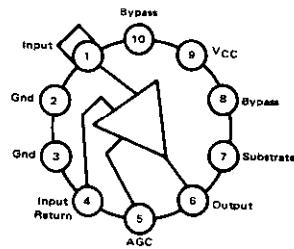
... a versatile, common-emitter, common-base cascode circuit for use in communications applications. See Application Note AN-215A for additional information.

- Constant Input Impedance over entire AGC range
- Extremely Low y_{12} - 4.3 μ mhos at 60 MHz
- High Power Gain - 30 dB @ 60 MHz (0.5 MHz BW)
- Good Noise Figure - 5 dB @ 60 MHz

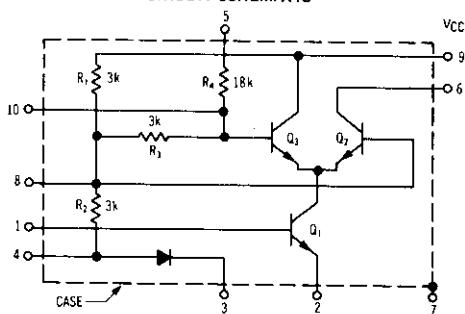
MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Power Supply Voltage, Pin 9	V _{CC}	20	Vdc
AGC Supply Voltage	V _{AGC}	20	Vdc
Input Differential Voltage, Pin 1 to Pin 4 ($R_S = 500$ ohms)	V _{ID}	± 5.0	V(rms)
Power Dissipation (Package Limitation)	P _D		
Metal Can		680	mW
Derate above $T_A = +25^\circ\text{C}$		4.6	mW/ $^\circ\text{C}$
Flat Package		500	mW
Derate above $T_A = +25^\circ\text{C}$		3.3	mW/ $^\circ\text{C}$
Operating Ambient Temperature Range	T _A	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	T _{stg}	-65 to +150	$^\circ\text{C}$

G SUFFIX
METAL PACKAGE
CASE 603B



CIRCUIT SCHEMATIC



CIRCUIT DESCRIPTION

The MC1550 is built with monolithic fabrication techniques utilizing diffused resistors and small-geometry transistors. Excellent AGC performance is obtained by shunting the signal through the AGC transistor Q₅ maintaining the operating point of the input transistor Q₁. This keeps the input impedance constant over the entire AGC range.

The amplifier is intended to be used in a common-emitter, common-base configuration (Q₁ and Q₂) with Q₅ acting as an AGC transistor. The input signal is applied between pins 1 and 4, where pin 4 is ac-coupled to ground. DC source resistance between pins 1 and 4 should be small (less than 100 ohms). Pins 2 and 3 should be connected together and grounded. Pins 8 and 10 should be bypassed to ground. The positive supply voltage is applied at pin 9 and at higher frequencies, pin 9 should also be bypassed to ground. The output is taken between pins 6 and 9. The substrate is connected to pin 7 and should be grounded. AGC voltage is applied to pin 5.

ELECTRICAL CHARACTERISTICS ($V^+ = +6$ Vdc, $T_A = +25^\circ\text{C}$)

Characteristic	Conditions	Figure	Symbol	Min	Typ	Max	Unit
DC CHARACTERISTICS							
Output Voltage	$V_{AGC} = 0$ Vdc $V_{AGC} = +6$ Vdc	1	V_O	3.80 5.90	—	4.65 6.00	Vdc
Test Voltage	$V_{AGC} = 0$ Vdc $V_{AGC} = +6$ Vdc	1	V_8	2.85 3.25	—	3.40 3.80	Vdc
Supply Drain Current	$V_{AGC} = 0$ Vdc $V_{AGC} = +6$ Vdc	1	I_D	—	—	2.2 2.5	mAdc
AGC Supply Drain Current	$V_{AGC} = 0$ Vdc $V_{AGC} = +6$ Vdc	1	I_{AGC}	—	—	-0.2 0.18	mAdc

SMALL-SIGNAL CHARACTERISTICS

Small-Signal Voltage Gain	$f = 500$ kHz	2	A_V	22	—	29	dB
Bandwidth	-3.0 dB	2	BW	22	—	—	MHz
Transducer Power Gain	$f = 60$ MHz, $BW = 6$ MHz $f = 100$ MHz, $BW = 6$ MHz	3	A_P	—	25 21	—	dB

TYPICAL CHARACTERISTICS
($V_{CC} = 6.0$ Vdc, $T_A = +25^\circ\text{C}$ unless otherwise noted.)

FIGURE 1 – DC CHARACTERISTICS TEST CIRCUIT

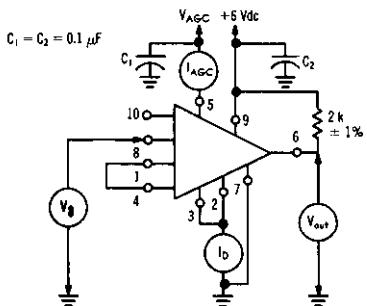


FIGURE 2 – VOLTAGE GAIN AND BANDWIDTH TEST CIRCUIT

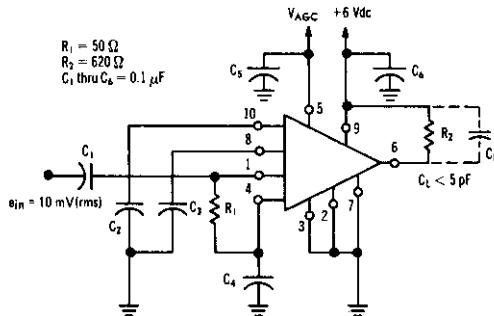


FIGURE 3 – POWER GAIN TEST CIRCUIT @ 60 MHz

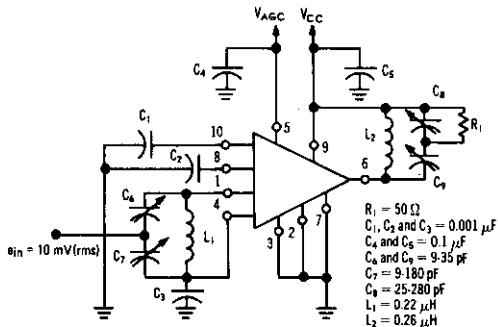
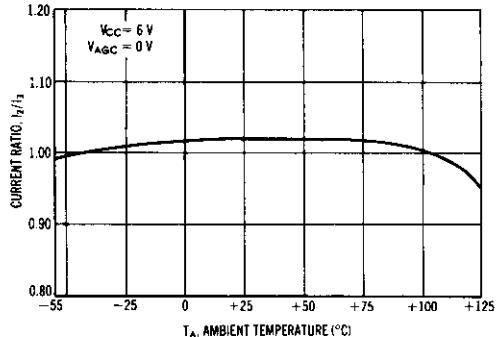


FIGURE 4 – DRAIN CURRENT TEMPERATURE CHARACTERISTICS



TYPICAL CHARACTERISTICS (continued)

FIGURE 5 – INPUT RESISTANCE AND CAPACITANCE versus FREQUENCY

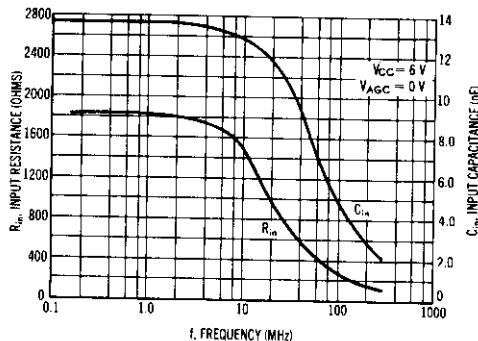


FIGURE 6 – INPUT RESISTANCE AND CAPACITANCE versus AGC VOLTAGE

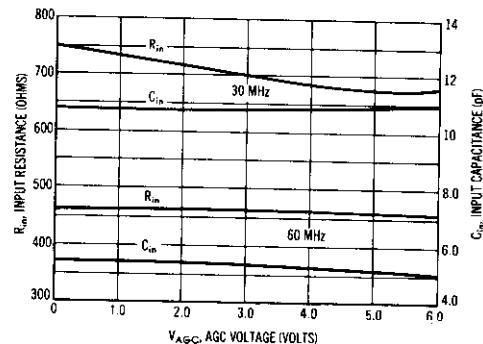


FIGURE 7 – OUTPUT RESISTANCE AND CAPACITANCE versus FREQUENCY

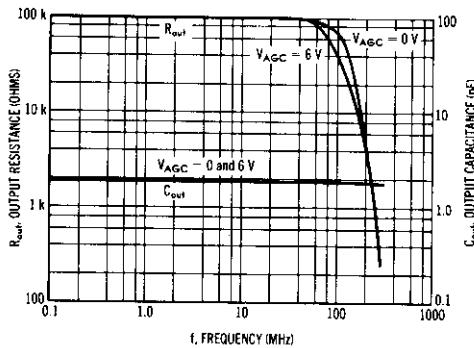


FIGURE 8 – OUTPUT RESISTANCE AND CAPACITANCE versus AGC VOLTAGE

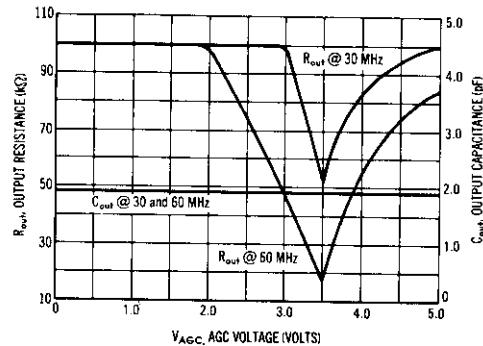


FIGURE 9 – MAXIMUM TRANSDUCER POWER GAIN versus FREQUENCY

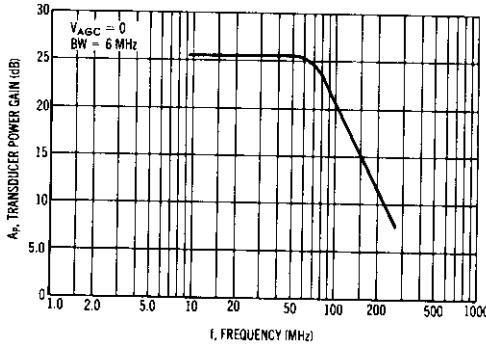
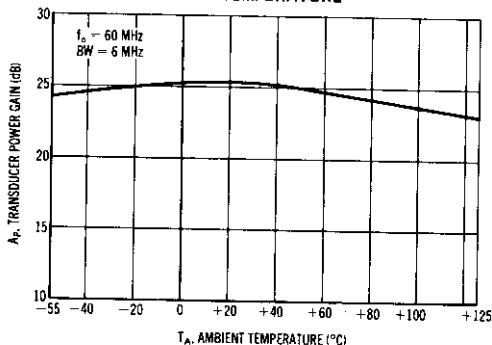


FIGURE 10 – TRANSDUCER POWER GAIN versus TEMPERATURE



TYPICAL CHARACTERISTICS (continued)

FIGURE 11 – TRANSDUCER POWER BANDWIDTH versus AGC VOLTAGE

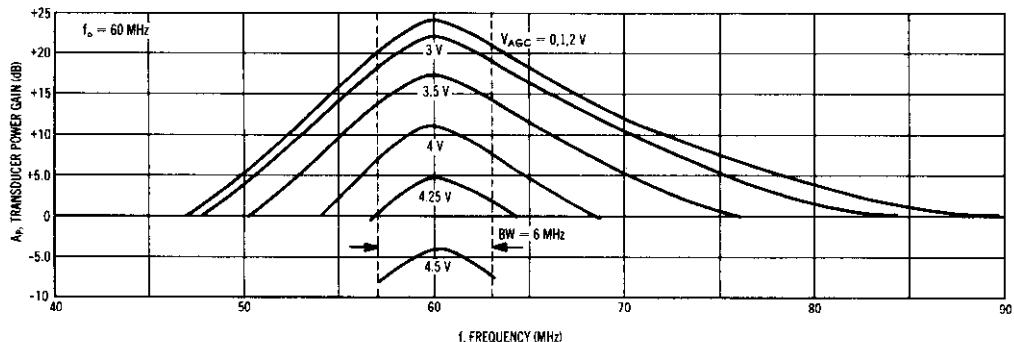


FIGURE 12 – NOISE FIGURE AND OPTIMUM SOURCE RESISTANCE versus FREQUENCY

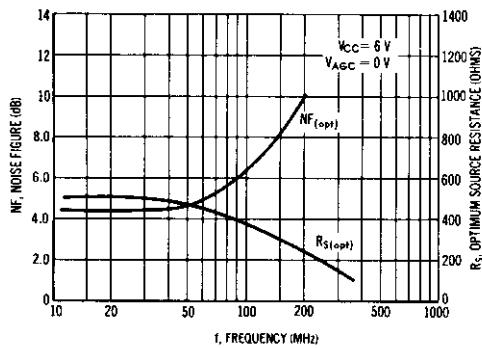
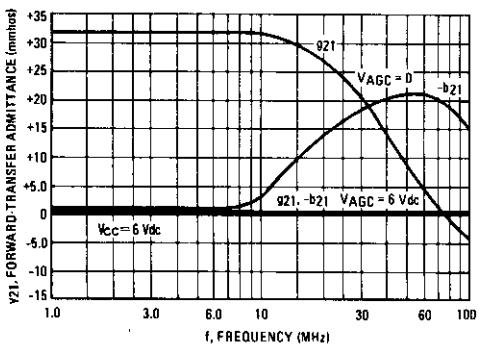
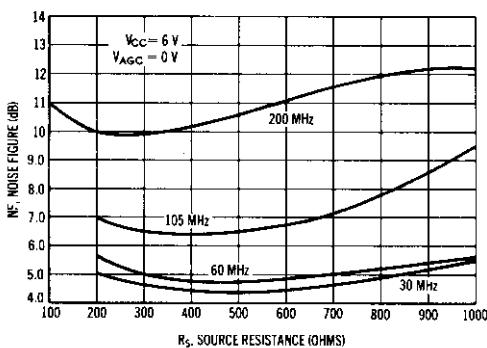
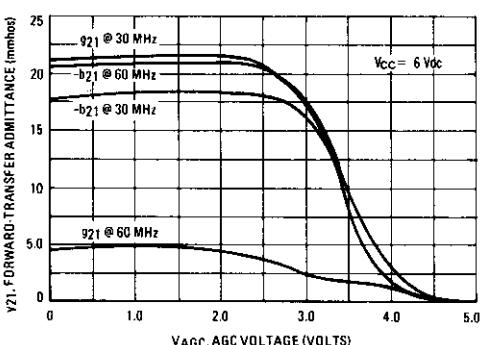
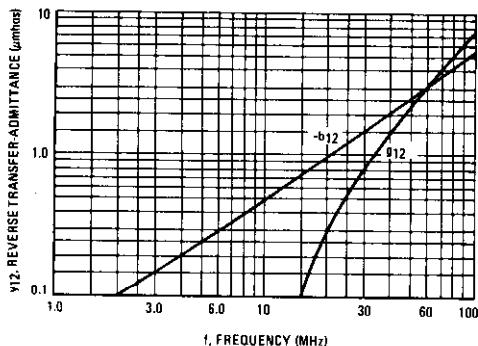
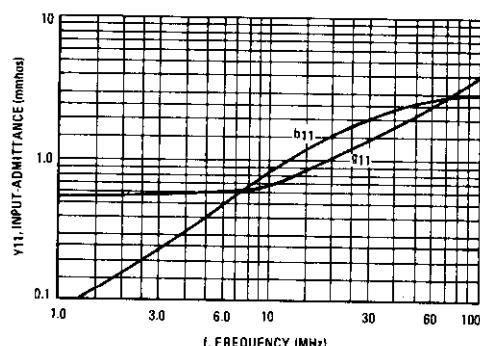
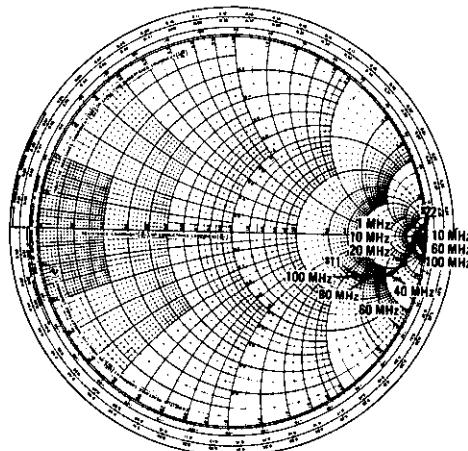
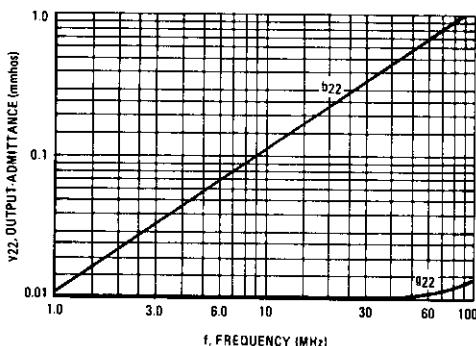
FIGURE 14 – y_{21} , FORWARD-TRANSFER ADMITTANCE versus FREQUENCY

FIGURE 13 – NOISE FIGURE versus SOURCE RESISTANCE

FIGURE 15 – y_{21} , FORWARD-TRANSFER ADMITTANCE versus AGC VOLTAGE

TYPICAL CHARACTERISTICS

(V_{CC} = 6.0 Vdc, T_A = +25°C unless otherwise noted.)FIGURE 16 - Y₁₂, REVERSE TRANSFER-ADMITTANCE versus FREQUENCYFIGURE 17 - Y₁₁, INPUT-ADMITTANCE versus FREQUENCYFIGURE 19 - s₁₁ AND s₂₂, INPUT AND OUTPUT REFLECTION COEFFICIENTFIGURE 18 - Y₂₂, OUTPUT-ADMITTANCE versus FREQUENCY

TYPICAL CHARACTERISTICS (continued)
 ($V_{CC} = 6.0$ Vdc, $T_A = +25^\circ\text{C}$ unless otherwise noted.)

FIGURE 20 – s_{11} , INPUT REFLECTION COEFFICIENT versus FREQUENCY

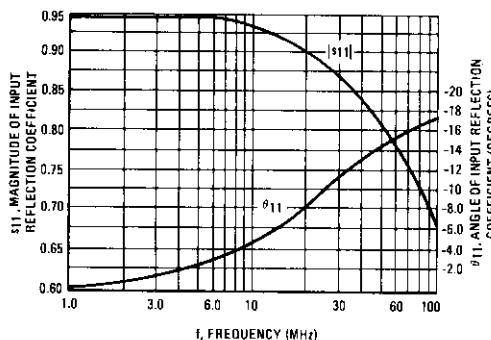


FIGURE 21 – s_{22} , OUTPUT REFLECTION COEFFICIENT versus FREQUENCY

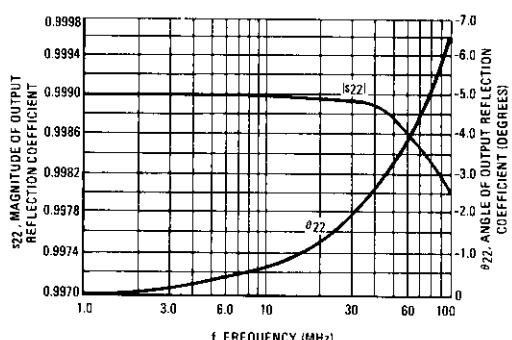


FIGURE 22 – s_{21} , FORWARD TRANSMISSION COEFFICIENT (GAIN)

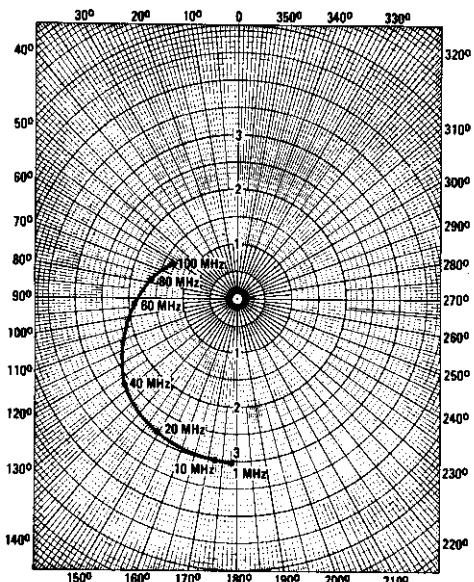


FIGURE 23 – s_{12} , REVERSE TRANSMISSION COEFFICIENT (FEEDBACK)

